

IS61WV51232 - 512K x 32 HIGH SPEED ASYNCHRONOUS SRAM

FEATURES

- High-speed access times:
8, 10, 20 ns
- High-performance, low-power CMOS process
- Multiple power and ground pins for greater noise immunity
- Easy memory expansion with \overline{CE} and \overline{OE} options
- \overline{CE} power-down
- Industrial and Automotive Temperature Support
- Lead-free available
- Single power supply
 - V_{DD} 1.65V to 2.2V (IS61WV51232Axx)
speed = 20ns for V_{DD} 1.65V to 2.2V
 - V_{DD} 2.4V to 3.6V (IS61/64WV51232Bxx)
speed = 10ns for V_{DD} 2.4V to 3.6V
speed = 8ns for V_{DD} 3.3V \pm 5%
- Packages available:
90-ball miniBGA (8mm x 13mm)

APPLICATIONS

The device is an ideal solution for x32 applications and well suited for customers requiring simple Asynchronous interface. The device is used in a variety of applications including:

- Industrial
- Automotive
- Telecom
- Networking

STATUS

S=NOW, Prod = Q4/2007

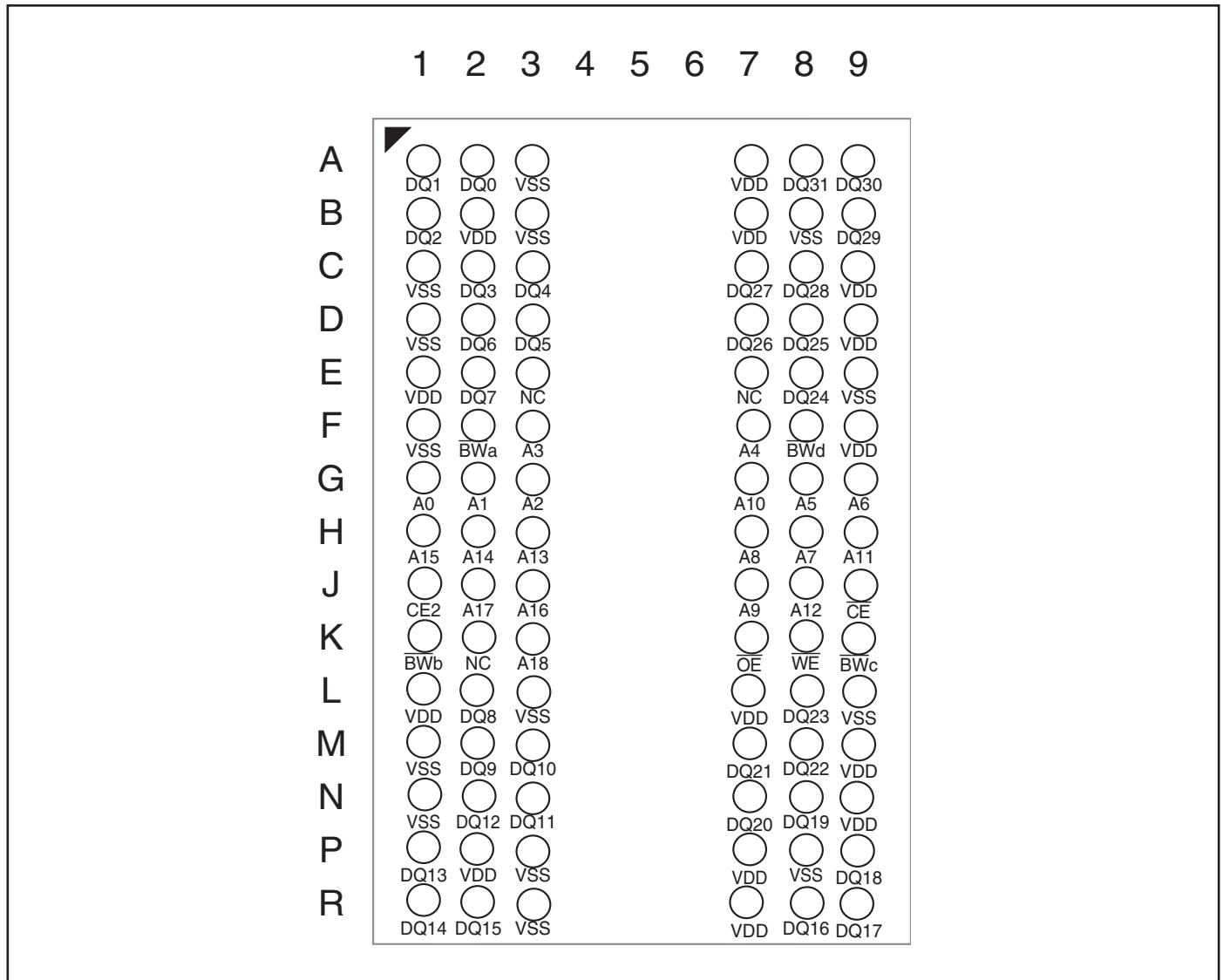
PRICING

- Budgetary Pricing: \$9.95 each (for 10K quantity)



PIN CONFIGURATION

PACKAGE CODE: B 90 BALL FBGA (Top View) (8.00 mm x 13.00 mm Body, 0.8 mm Ball Pitch)



PIN DESCRIPTIONS

A0-A18	Address Inputs
DQx	Data I/O
\overline{CE} , CE2	Chip Enable Input
\overline{OE}	Output Enable Input
\overline{WE}	Write Enable Input
\overline{BWx} (x=a-d)	Byte Write Control
V _{DD}	Power
V _{SS}	Ground
NC	No Connection